

This is the Author's Pre-print version of the following article: *Y. Velázquez-Galván, J. de la Torre Medina, L. Piraux, A. Encinas, Robustness of the enhanced magnetic anisotropy in Ni nanowires regardless of the deposition potential, Journal of Magnetism and Magnetic Materials, Volume 497, 2020, 165992*, which has been published in final form at: <https://doi.org/10.1016/j.jmmm.2019.165992>

© 2020 This manuscript version is made available under the Creative Commons Attribution-NonCommercial-NoDerivatives 4.0 International (CC BY-NC-ND 4.0) license <http://creativecommons.org/licenses/by-nc-nd/4.0/>

Robustness of the enhanced magnetic anisotropy in Ni nanowires regardless of the deposition potential

Y. Velázquez-Galván

División de Materiales Avanzados, Instituto Potosino de Investigación Científica y Tecnológica A. C., Camino a la Presa 2055, 78216 San Luis Potosí, SLP, México

J. de la Torre Medina

Instituto de Investigaciones en Materiales / Unidad Morelia, Universidad Nacional Autónoma de México. Antigua Carretera a Pátzcuaro No. 8701 Col. Ex Hacienda de San José de la Huerta, 58190 Morelia, Mexico

L. Piraux

Institute of Condensed Matter and Nanosciences, Université catholique de Louvain, Place Croix du Sud 1, B-1348, Louvain-la-Neuve, Belgium

A. Encinas

División de Materiales Avanzados, Instituto Potosino de Investigación Científica y Tecnológica A. C., Camino a la Presa 2055, 78216 San Luis Potosí, SLP, México

Abstract

The effects of the deposition potential on the structural and magnetic properties of Ni nanowires with a diameter of 40 nm and lengths varying from 16 up to 56 μm have been studied. The results show that very long NWs exhibit a large enhancement of their uniaxial magnetic anisotropy. This anisotropy reaches values as high as $1.6 \times 10^6 \text{ erg/cm}^3$ that is comparable with the value due to the magnetostatic anisotropy contribution ($\approx 5 \times 10^6 \text{ erg/cm}^3$) and as shown from the results this large anisotropy is practically insensitive to the deposition potential. Moreover, as shown on shorter NWs, this enhancement of the anisotropy is not observed and interestingly the potential does induce

*Corresponding author

Email address: yenni.velazquez.g@gmail.com (Y. Velázquez-Galván)

structural changes that relate to their magnetic properties. The enhanced anisotropy observed in long NWs is a robust effect as it is independent of the potential, making this property attractive for applications where high uniaxial anisotropies are required.

Keywords: Nanowires, Nickel, enhanced anisotropy, confinement, deposition potential

1. Introduction

Electrodeposited magnetic NWs are of great scientific and technological interest due to their simple cylindrical geometry and relative ease of fabrication. Electrochemical deposition into nanoporous templates has proven to be a very versatile approach to fabricate a wide variety of nanostructures based on cylindrical wires with novel physicochemical properties [1, 2, 3, 4, 5, 6, 7].

Nickel NWs are amongst the most interesting and promising magnetic NWs, due to their environmentally benign nature, low cost and availability. At present there are numerous reports on their physicochemical properties that show their potential. Furthermore, oxidised Ni NWs have been shown to possess great potential for memristive elements as well as for their use as electrochemical electrodes for energy (batteries [8] and supercapacitors [9, 10]) and sensing (glucose [11, 12, 13] and urea [14, 15, 16]).

The magnetic and electronic properties of Ni NWs are strongly dependent on their crystalline structure, which in turn are related to their use in different applications. Numerous studies have shown that it is possible to control the magnetic properties of these systems changing a variety of parameters as the host matrix [17, 18, 19, 20], diameter [21, 22, 23, 24, 25], length or aspect ratio [26, 27] as well as the pH [28, 29, 30], temperature [31] and applied potential [32, 33, 34, 35].

Recently it was shown that very long Ni nanowires (with lengths of about 10-80 μm) grown in anodic aluminium oxide (AAO) templates exhibit a very large enhanced uniaxial magnetic anisotropy [36]. This anisotropy was shown to originate from the combination of two effects. The first one is related to a two stage growth mechanism in which the NWs first grow with a polycrystalline microstructure which after reaching a certain length evolves to a single-crystalline [110] structure [17, 37, 38]. The second effect was related to a residual stress on NWs that results from their confined growth which increases as the diameter decreases and as the crystal texture is enhanced

30 [39, 40]. This enhanced anisotropy was reported to be as high as 1.4×10^6
31 erg/cm^3 (or 5.7 kOe) which is comparable to the effective magnetic anisotropy
32 of Co. Such large anisotropy opens up many interesting perspectives where
33 nanomaterials with high uniaxial anisotropies are desirable. This is further
34 complemented by other valuable properties of Ni, like its availability, low cost
35 compared with Co and greater stability as compared to Fe. Furthermore, this
36 enhanced anisotropy was shown to depend on geometrical parameters such
37 as NW diameter and length which relate to the microstructure [22, 41, 42].
38 In this sense, as shown by several studies, the microstructural characteristics
39 of electrodeposited Ni NWs depends strongly on the deposition potential
40 [38, 32, 33]. However, most (if not all) of the studies regarding the influence
41 of the deposition potential on the structural and magnetic properties have
42 been limited of short Ni NWs, in the range 6–12 μm [30, 43, 44, 45, 46].
43 So in this sense, analyzing the effect of the deposition potential on very
44 long Ni NWs on the microstructural and magnetic properties is relevant
45 since there is no information regarding its effect on the value of the enhanced
46 uniaxial magnetic anisotropy. In addition also seeking to determine if similar
47 effects can be obtained in other templates, particularly in polycarbonate (PC)
48 membranes which are also interesting due to their lower pore densities and
49 their flexibility.

50 In the present work we have studied the influence of the deposition poten-
51 tial on the structural and magnetic properties of arrays of Ni NWs electrode-
52 posed in porous AAO and PC membranes. We have shown that neither the
53 crystal orientation nor the large magnetic anisotropy of Ni NWs embedded in
54 AAO membranes are significantly perturbed by the reduction potential. This
55 magnetic anisotropy reaches a value as large as $1.6 \times 10^6 \text{ erg/cm}^3$ (6 kOe),
56 which is consistent with previous results [36]. Conversely, Ni NWs embedded
57 in PC membranes do not show an enhanced anisotropy. These NWs have
58 lower length ($\sim 15\mu\text{m}$) and they show significant changes in their structural
59 and magnetic properties induced by the electrodeposition potential. These
60 different behaviors are attributed to the two stage electrodeposition growth
61 mechanism, which is related to the type of host template used for the growth
62 of the NWs, as they limit the NW lengths. Therefore, the fundamental
63 outcome of this work is the possibility of fabricate arrays of Ni NWs with a
64 large uniaxial magnetic anisotropy independently of the deposition potential,
65 allowing their fabrication using less restrictive deposition conditions.

66 2. Materials and methods

67 Ni NWs have been grown by electrodeposition into low pore density poly-
68 carbonate membranes (it4ip S. A.) as well as in high pore density anodic alu-
69 minium oxide membranes (Synkera Technologies, Inc.). PC based Ni NWs
70 have a diameter of 40 nm, thickness of 20 μm and membrane porosity (NW
71 packing fraction) $P=5\%$ corresponding to an average interwire distance of
72 $d_0=165$ nm, while NWs grown in AAO membranes have a diameter of 35
73 nm, thickness of 90 μm , $P=12\%$ and $d_0=95$ nm. All depositions were done
74 at room temperature in the potentiostatic mode using a Ag/AgCl reference
75 electrode and a Pt counter electrode. For the electrodeposition process, a
76 Cr(5nm)/Cu(600nm)/Au(300nm) layer was evaporated on one side of the
77 membrane in order to serve as a cathode. The electrolyte contained 262.84
78 g/l $\text{NiSO}_4 \cdot 6\text{H}_2\text{O}$ + 30 g/l H_3BO_3 with a pH value of 4.0. For both PC
79 and AAO based nanowire samples, the electrodeposition was carried out at
80 constant deposition potentials of -1.0, -1.05, -1.1, -1.2, -1.3, -1.4 and -1.5 V.

81 Characterization of the crystal structure was made by X-Ray Diffraction
82 (XRD) with a $\text{CuK}\alpha$ radiation ($\lambda = 1.54\text{\AA}$) using a Rigaku smartkab
83 X-ray diffractometer. The magnetic properties of the Ni NWs have been
84 measured at room temperature using magnetometry and ferromagnetic reso-
85 nance (FMR). The hysteresis loops were obtained by applying a magnetic
86 field parallel to the wire axis, using an Alternating Gradient Magnetometer
87 with a maximum applied field of ± 14 kOe. Field-swept FMR was done
88 using a micro-strip line configuration with the external field applied paral-
89 lel to the wire axis [47]. The absorption spectra are recorded at a constant
90 excitation frequency while the applied field is swept from 10 kOe down to
91 zero field. For a given excitation frequency, the resonance field corresponds
92 to the minimum of the spectra. Then, to construct the dispersion relation,
93 the absorption spectra are measured and recorded using different excitation
94 frequencies.

95 3. Results

96 3.1. Effect of the potential in AAO based-Ni NWs

97 Figures 1 (a) and (b) show SEM micrographs of the cross-sectional view
98 of electrodeposited Ni NWs embedded in AAO membrane. As seen in the
99 figure, the nanowires grow perpendicular to the Au layer inside the pores of

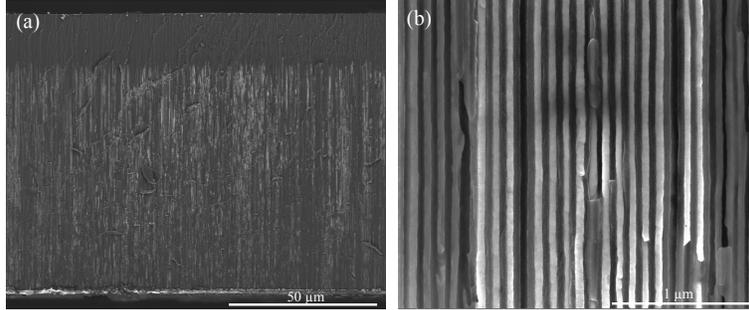


Figure 1: (a) Low and (b) high magnification SEM micrographs of the cross-section of electrodeposited Ni NWs embedded in AAO membrane.

100 the membrane. Further, it is possible to observe the length of the nanowires
 101 and the membrane thickness.

102 Figure 2 shows the XRD measurements obtained in Ni NW arrays grown
 103 using AAO templates at different deposition potentials ranging from -1.0 to
 104 -1.5 V. As seen in the figure, Ni NWs grown in AAO templates show little
 105 sensitivity to the deposition potential, in all cases a strong [110] texture due
 106 to the presence of the peak to the (220) plane is observed. Furthermore, the
 107 (200) reflection is also noticeable but its amplitude is very small in all cases.
 108 On the other hand, the contribution due to the Au layer deposited in one
 109 side of the membrane is perceptible and its intensity depends on how much
 110 it can be removed from this layer before characterizing the samples. From
 111 the results it follows that the texture quality is best at $E=-1.0$ to -1.05 V.

112 Texture analysis was done in order to quantify this strong preferential
 113 crystallographic orientation. The texture coefficients were determined using
 114 the XRD patterns and Harris formula defined as [48]

$$TC(hkl)_i = \frac{\frac{I(hkl)_i}{I_0(hkl)_i}}{\frac{1}{N} \sum_n \frac{I(hkl)_n}{I_0(hkl)_n}}, \quad (1)$$

115 where $TC(hkl)$ is the texture coefficient of (hkl) plane, $I(hkl)_i$ is the measured
 116 relative intensity, $I_0(hkl)$ is the relative intensity of the corresponding plane
 117 for a polycrystalline sample and N is the total number of reflections. In this
 118 work, the Ni NWs were indexed using the 00-004-0850 card (ICDD PDF-4
 119 database)[49]. The texture coefficient with values larger than the unity indi-
 120 cates a preferred orientation of the nanowire arrays along the corresponding

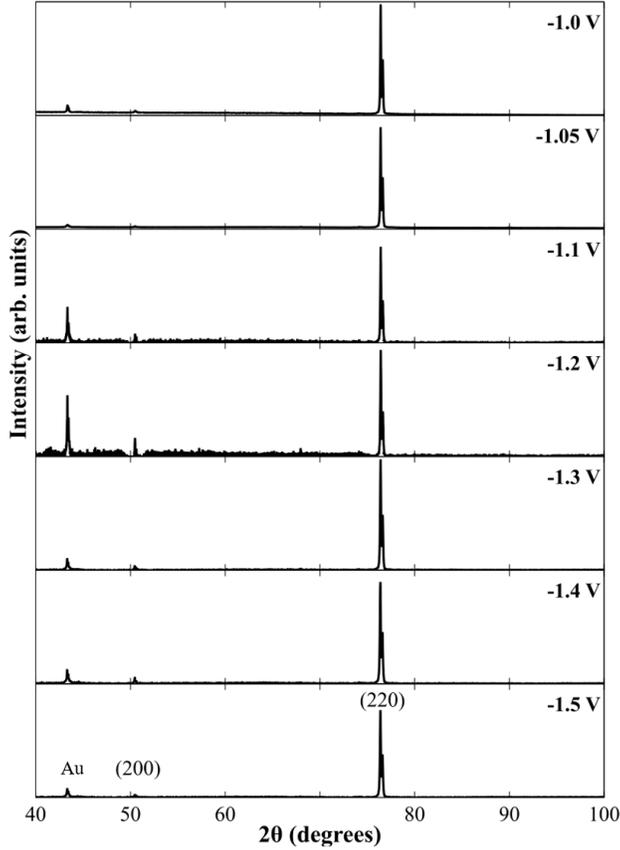


Figure 2: XRD patterns from Ni NWs embedded in AAO membranes grown at deposition potentials of $E = -1.0, -1.05, -1.1, -1.2, -1.3, -1.4$ and -1.5 V.

121 plane. Further, the maximum value of $TC(hkl)$ is N which implies that the
 122 wires possess a complete preferential orientation [50].

123 The results obtained using XRD patterns of figure 2 give $TC(200)$ values
 124 ranging from 0.04 to 0.16 and $TC(220)$ values around 1.9 for Ni NWs grown
 125 in AAO membranes. These texture coefficient values are consistent with a
 126 strong texture with preferential crystallographic orientation along the [110]
 127 direction regardless of the deposition potential.

128 Figure 3 (a) shows the hysteresis loops measured with the external field
 129 applied parallel to the axis of the NWs embedded in AAO templates at
 130 deposition potentials of $E = -1.0, -1.2$ and -1.5 V. Furthermore, figures 3 (b-

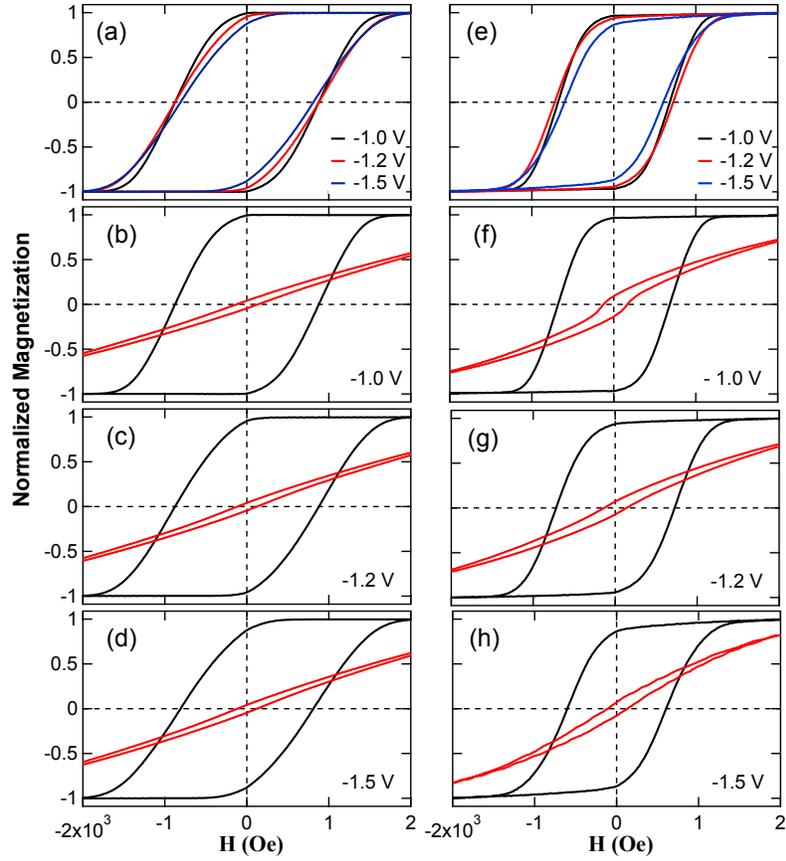


Figure 3: Hysteresis loops measured with the field applied parallel to the NW axis for Ni wires grown at deposition potentials of $E = -1.0, -1.2$ and -1.5 V vs Ag/AgCl in (a) AAO and (e) PC templates. Comparison of the hysteresis loops measured with the magnetic field applied parallel and perpendicular to the NW axis for the Ni NWs deposited in (b-d) AAO and (f-h) PC templates.

131 d) show the hysteresis loops obtained by applying the magnetic field parallel
 132 and perpendicular to the NWs axis for the samples deposited at potentials
 133 $E = -1.0, -1.2$ and -1.5 V in AAO templates. The remanence (M_r/M_s) as well
 134 as the coercive field (H_c) show slight changes when the potential becomes
 135 more negative, suggesting a decrease in the total anisotropy.

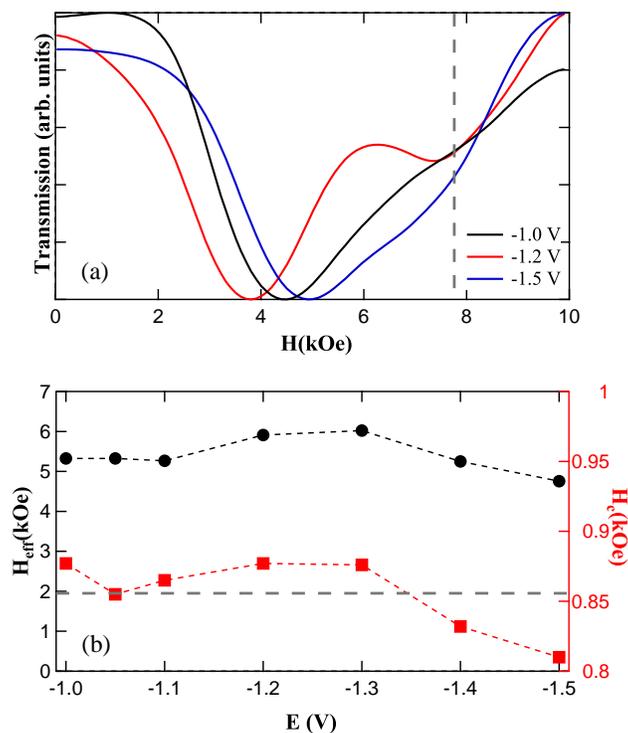


Figure 4: (a) Ferromagnetic resonance spectra recorded at 30 GHz in Ni-AAO NWs ($d=35$ nm and $P=12\%$) obtained using deposition potentials of $E=-1.0, -1.2$ and -1.5 V, the vertical dashed line corresponds to the resonance field given by equation (2) and, (b) comparison between the effective anisotropy field and the coercive field with variation of electrodeposition potential, the horizontal dashed line indicates the MS anisotropy contribution.

136 Figure 4 (a) shows typical FMR spectra recorded at 30 GHz for the same
 137 samples as in Fig. 3. As seen in the figure, the lineshape of the FMR spectra
 138 changes significantly as a function of the deposition potential. In all cases,
 139 the linewidth is large and two absorption peaks can be identified, which is
 140 more evident in the $E=-1.2$ V sample. The presence of two absorption peaks

141 in the FMR spectra indicates the presence of two Ni volume fractions each
 142 with different magnetic anisotropy. Moreover, the amplitude of these peaks
 143 are proportional to the individual volume fractions [36]. As seen in the figure,
 144 all the spectra show a dominant absorption peak located at lower field values,
 145 while the second low-intensity peak appears at higher fields.

146 In order to relate the position of these peaks with their corresponding
 147 magnetic anisotropies, consider the FMR dispersion relation for cylindrical
 148 NWs with the field applied parallel to the wires,

$$\frac{f}{\gamma} = H_r + H_{eff}, \quad (2)$$

149 where f is the excitation frequency, $\gamma=3.09$ GHz/kOe is the gyromagnetic ratio
 150 for Ni [51] and H_{eff} is the effective field. The effective field includes all the
 151 magnetic anisotropy contributions as well as the dipolar interaction between
 152 NWs. For magnetic NWs, the magnetic anisotropy can have shape, magne-
 153 tocrystalline (MC) and magnetoelastic (ME) contributions. For the partic-
 154 ular case of very long Ni NWs where there are no MC or ME contributions,
 155 the effective field is purely magnetostatic (MS) since it contains only the
 156 shape anisotropy ($H = 2\pi M_s$) and the dipolar interaction ($H = -6\pi M_s P$),
 157 namely [47],

$$H_{ms} = 2\pi M_s(1 - 3P), \quad (3)$$

158 where $M_s=485$ emu·cm⁻³ is the saturation magnetization of Nickel [52]. The
 159 MS field serves as a reference to analyze the position of the FMR peaks.
 160 For the Ni NWs grown in AAO, the packing fraction is $P=12\%$ so their
 161 resonance field at 30 GHz is $H_r=7.76$ kOe, which corresponds to the vertical
 162 dashed line in Fig. 4(a). From the figure it is clear that the high-field
 163 low amplitude FMR peaks are located around the expected value for purely
 164 MS Ni nanowires. The major absorption peaks, with lower resonance fields
 165 imply an additional anisotropy contribution that leads to a larger effective
 166 field. The field difference between the resonance fields of these peaks and
 167 the position of the MS resonance provide an estimate of the magnitude of
 168 this additional anisotropy contribution, which in this case is in the order
 169 of 3-4 kOe. This enhanced anisotropy in Ni NWs grown in AAO templates
 170 originates from a residual stress due to the confinement in small pore diameter
 171 templates [36]. This large anisotropy was observed in all the Ni AAO samples.
 172 Figure 4 (b) shows the effective field obtained using Eq. (2) and the coercive
 173 field of the Ni AAO samples as a function of the deposition potential. The

174 dashed horizontal line is the MS effective field for a Ni NWs array with a
 175 packing fraction of 12%. The effective field increases up to a maximum value
 176 as the potential increases from -1.0 V up to -1.2 V, which is followed by a
 177 decrease of about 1.3 kOe as the potential further increases. Furthermore,
 178 it is observed that both H_c and H_{eff} show a similar behavior due to the
 179 deposition potential. This shows that the enhanced anisotropy in AAO Ni
 180 NWs is little sensitive to the deposition potential. Indeed, for all deposition
 181 potentials a very large anisotropy is observed which varies little. Comparing
 182 the measured effective field values with that expected for the MS case, an
 183 enhancement of 3-4 kOe is confirmed. Considering the same packing fraction,
 184 this value is comparable to the MS field of cobalt obtained using Eq. (3) and
 185 $M_s=1400 \text{ emu}\cdot\text{cm}^{-3}$, which is around 5.6 kOe.

186 3.2. Effect of the potential in PC-based Ni NWs

187 Figure 5 shows the XRD measurements corresponding to Ni NW arrays
 188 grown using PC templates at different deposition potentials. As observed, the
 189 crystalline structure of these NWs is polycrystalline as suggested by the pres-
 190 ence of (220) and (111) planes in the diffractograms. Nickel nanowires grown
 191 at low reduction potentials in PC membranes are highly polycrystalline, with
 192 a crossover at -1.3 V where they become mostly single-crystalline with pref-
 193 erential crystal orientation along the [110] direction. Further increasing the
 194 deposition potential, at -1.4 V and -1.5 V, there is a shift on the preferential
 195 orientation from [110] to [111] direction because the peak corresponding to
 196 the (111) plane becomes more pronounced and the (220) plane is almost neg-
 197 ligible. No changes are observed in the weak (200) plane due to the applied
 198 potential. These diffraction peaks are in agreement with 00-004-0850 card
 199 (ICDD PDF-4 database) [49].

200 These features have been corroborated with a quantitative analysis of
 201 the texture coefficients determined using Eq. (1) with $N=4$ for all the XRD
 202 patterns of figure 5. The results are summarized in Table 1 for (111) and (220)
 203 planes. In this case, the texture coefficient values are greater than one for
 204 TC(111) and TC(220). The texture coefficient values of the other reflections
 205 are less than one for all the arrays and therefore are not shown in Table 1.
 206 It shows that Ni NWs arrays deposited in PC membranes can be obtained
 207 with a texture having either a (111) or a (220) preferential orientation. Ni
 208 NWs embedded in PC membranes grown at low deposition potentials present
 209 a texture that appears to be approximately constant along the (220) plane.
 210 The maximum texture value is obtained for the arrays deposited at -1.3 V

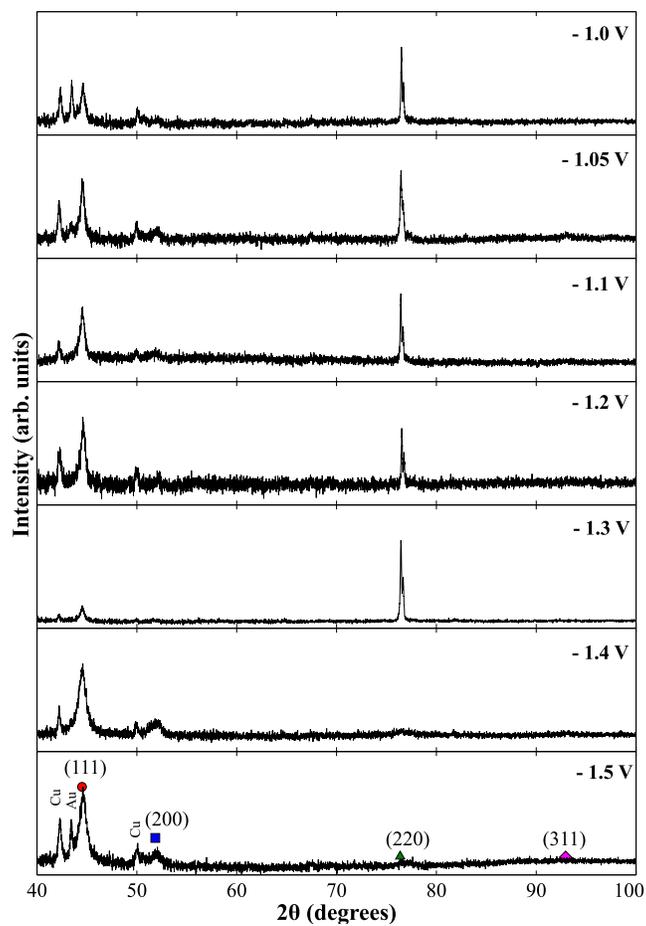


Figure 5: XRD patterns from Ni NWs embedded in PC membranes grown at deposition potentials of $E = -1.0, -1.05, -1.1, -1.2, -1.3, -1.4$ and -1.5 V. The dots positioned on the graph for the -1.5 V sample correspond and are in agreement with the expected position and intensity of the (111), (200) and (220) peaks for polycrystalline Ni [49].

211 which indicates a strong texture with preferential crystal orientation along
 212 the [110] direction. On the other hand, NWs deposited at higher potentials
 213 exhibit a texture along the [111] direction as expected.

Table 1: Texture coefficient values for Ni NWs embedded in PC membranes grown at different deposition potentials.

$E(V)$	TC(111)	TC(220)
-1.0	0.30	2.88
-1.05	0.47	2.55
-1.1	0.44	2.52
-1.2	0.55	2.29
-1.3	0.17	3.33
-1.4	1.11	1.20
-1.5	1.23	0.98

214 Figure 3 (e) shows the hysteresis loops of Ni NWs grown in PC templates
 215 at deposition potentials of $E=-1.0$, -1.2 and -1.5 V with the external field
 216 applied along the NWs axis. As seen in the figure, small changes in both the
 217 remanence and coercive field appear as the deposition potential is modified,
 218 which is similar to the behavior observed in the AAO based samples. As a
 219 comparison, the hysteresis loops with the field applied parallel and perpen-
 220 dicular to the NWs grown using a deposition potential of $E=-1.0$, -1.2 and
 221 -1.5 V grown in PC membranes are shown in figures 3 (f-h).

222 Complementary information about the magnetic anisotropy of these sys-
 223 tems is obtained from FMR spectra recorded at 26 GHz. As seen in Fig.
 224 6 (a), the absorption spectra display a complex non-symmetric lineshape, a
 225 small peak besides the main absorption peak is observed. This feature is
 226 more pronounced at lower potentials and indicates that Ni NWs present two
 227 different magnetic anisotropy contributions. Contrary to the case of the AAO
 228 based arrays of Ni NWs, all the PC based samples display a dominant ab-
 229 sorption peak at higher resonance fields. This opposite behavior arises from
 230 lower length of the NWs, then corroborating their polycrystallinity which is
 231 in good agreement with previous results [36]. The lineshape and position of
 232 the minimum of the FMR spectra shown in Fig. 6 (a) are consistent with
 233 a magnetic behavior characteristic of polycrystalline NWs that is mainly
 234 dominated by the MS contribution.

235 To further investigate the magnetic behavior of the PC based Ni NWs,

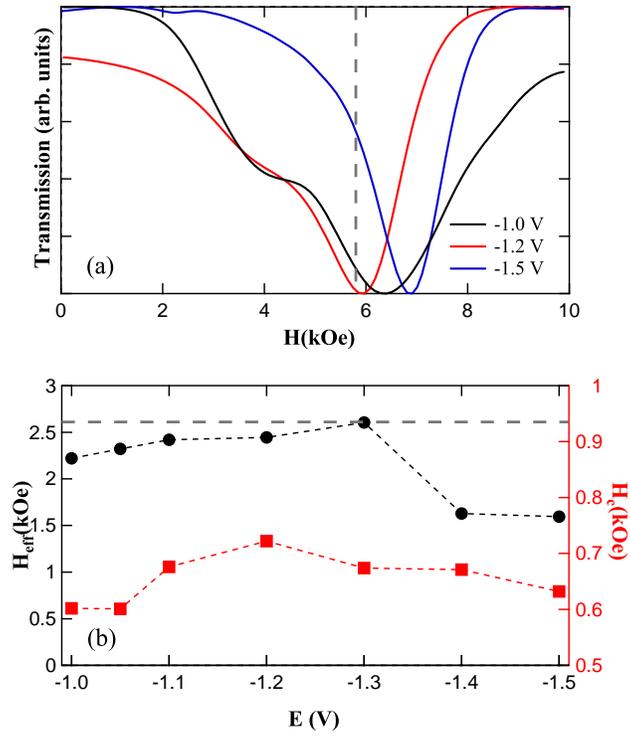


Figure 6: (a) Room temperature absorption spectra recorded at 26 GHz for Ni NWs grown in PC membranes ($d=40$ nm and $P=5\%$) obtained using deposition potentials of $E= -1.0$, -1.2 and -1.5 V, the vertical dashed line correspond at the resonance field with only MS anisotropy contribution and, (b) comparison between the effective anisotropy field and the coercive field as a function of the applied potential, the horizontal dashed line indicates the effective anisotropy field for systems with only MS anisotropy contributions.

236 Fig. 6 (b) shows the effective anisotropy field, H_{eff} , as a function of the
237 deposition potential determined using Eq. (2). For this system, the effective
238 field increases with the deposition potential toward the observed limiting
239 value for arrays of Ni NWs with purely MS anisotropy, at a potential of -
240 1.3 V. Then, this field decreases at values still lower than those for arrays
241 deposited at low potentials. Particularly, the effective field for the NWs
242 deposited at higher potentials is about 1 kOe lower than the expected value
243 due only to the MS anisotropy contribution (see the horizontal dashed line).
244 This decrease in magnetic anisotropy indicates the presence of an additional
245 anisotropy contribution that competes with the intrinsic MS anisotropy of
246 the NWs. That is, the shift in the anisotropy is related with the changes
247 observed in the crystalline structure, as seen in Fig. 5, where the (220)
248 texture disappears for Ni NWs deposited at higher potentials.

249 Furthermore, the variation of the coercive field with the reduction poten-
250 tial is displayed in Fig. 6 (b) for comparison. As seen, this field shows the
251 same trend as that for H_{eff} , where a maximum value is also observed around
252 -1.3 V. It can be also observed that although the coercive field presents small
253 variations due to the potential, its behavior is similar to the observed in
254 the effective field as expected. Moreover, H_c values of these NWs arrays
255 embedded in PC are slightly lower than the ones for NWs grown in AAO.

256 4. Discussion

257 The results presented show that Ni NWs embedded in AAO membranes
258 exhibit a large enhancement of the magnetic anisotropy [36]. This anisotropy
259 corresponds to values of the same order of magnitude and comparable to the
260 MS anisotropy for arrays of Co NWs (≈ 5600 Oe)[51, 23]. In contrast, for
261 arrays of short Ni NWs grown in PC membranes no such a large enhancement
262 of the magnetic anisotropy is observed.

263 As shown previously, the large positive enhancement of the magnetic
264 anisotropy of Ni NWs is strongly related with a two stage electrodeposition
265 growth of the Ni NWs [36, 53, 38, 33]. In the initial growth stage, the
266 orientation of the individual 3D nuclei is random, which is then followed by
267 an alignment of crystal planes along a preferential direction in a 2D growth
268 mode, leading to a structural transition of the nanowires from polycrystalline
269 to single-crystalline [54]. Therefore the texture of thicker metal deposit is
270 the result of a competitive growth mechanism occurring in the subsequent
271 growth stage to the coalescence stage.

272 The length of the polycrystalline segment can be obtained as a function of
 273 the total length of the NWs using the previously reported expression, given
 274 by

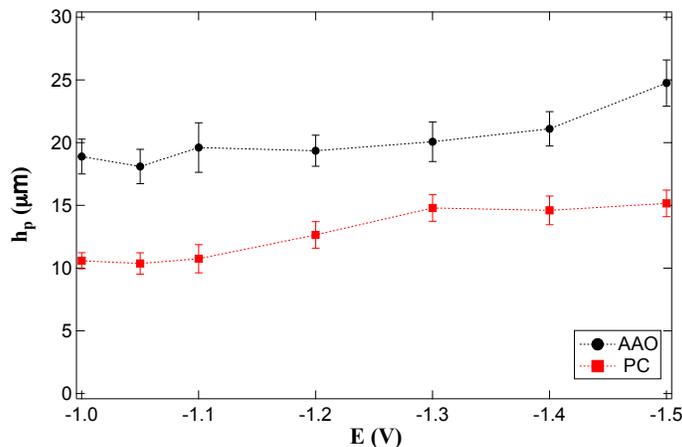


Figure 7: Length of the polycrystalline segment (h_p) as a function of the electrodeposition potential for Ni NWs grown in AAO and PC templates.

$$h_p = \frac{h}{1+r}, \quad (4)$$

275 where $r=h_s/h_p$ is the ratio between the length of the single and polycrys-
 276 talline segments [36]. The total length of the NWs, h , growth in AAO and
 277 PC membranes is $55 \mu\text{m}$ and $15 \mu\text{m}$, respectively. Figure 7 shows the varia-
 278 tion of h_p as a function of the electrodeposition potential for Ni NWs growth
 279 in AAO and PC membranes. As observed, the length of the polycrystalline
 280 segment increases with the potential for both systems. This behavior is in
 281 agreement with the decrease of the effective anisotropy field as the negative
 282 potential is increased, as seen in Fig. 4(b) and 6(b). Furthermore, in the
 283 case of NWs embedded in PC membranes h_p tends to a maximum value of
 284 about $15 \mu\text{m}$ at more negative potentials, which corresponds to almost the
 285 total length of the NWs ($h_p \approx h$).

286 The structural changes observed in the arrays of Ni NWs are further
 287 evidenced on their magnetic properties. Single-crystalline Ni NWs grown in
 288 AAO membranes display higher coercive field and remanence magnetization
 289 values than for polycrystalline Ni NWs grown in PC membranes, which is

290 consistent with previous works [33]. In general, the coercive field of Ni NWs
 291 in AAO membranes is larger than that of Ni NWs in PC membranes because
 292 the magnetic anisotropy of the former is much larger than that of the later.
 293 This difference in magnetic anisotropy is explained by the difference of the
 294 effective ME contributions in each system. The high aspect ratio of the NWs
 295 in AAO membranes confers a large positive ME effect that lies along the
 296 NWs axis and adds to the intrinsic MS contribution [36]. Conversely, the
 297 ME contribution of lower aspect ratio NWs in PC membranes is negligible
 298 and not necessarily lies along the NWs axis, so it competes with the MS
 299 contribution leading to a lower effective magnetic anisotropy.

300 To further investigate the additional magnetoelastic energy observed in
 301 both systems, the magnetoelastic field can be obtained directly from H_{eff} in
 302 Fig. 4 (b) and 6 (b), using the expression

$$H_{me} = H_{eff} - H_{ms}, \quad (5)$$

303 where H_{ms} is given in Eq. (3). However, the comparison of the additional
 304 ME anisotropy contribution with previous results is easier in terms of the
 305 ME energy [36], $K_{me} = (H_{me} \times M_s)/2$. Figure 8 shows K_{me} as a function
 306 of the deposition potential (E) of Ni NWs embedded in PC and AAO tem-
 307 plates, determined using Eq. (2). The behavior of K_{me} with E is similar for
 308 both systems, because the ME energy increases with E up to a maximum
 309 value at -1.3 V and then decreases at more negative values. The observed
 310 variation in K_{me} with E is of about 2.5×10^5 erg·cm⁻³. The very similar
 311 lineshape of K_{me} vs E for arrays of NWs in both PC and AAO membranes,
 312 suggests that such variation is due to the polycrystalline segment of the NWs.
 313 That is, in Ni NWs embedded in PC membranes there is not a subsequent
 314 single-crystalline segment that could explain such a variation. Therefore, the
 315 deposition potential is responsible of structural changes in the polycrystalline
 316 segment, which are related with the observed changes of K_{me} . Besides, for
 317 the case of long Ni NWs in AAO membranes, its effective ME energy is the
 318 superposition of two main ME contributions that arise from both crystalline
 319 segments. The single-crystalline segment leads to a large positive ME contri-
 320 bution, whereas the polycrystalline segment leads to a low ME contribution.
 321 Specifically, for the polycrystalline segment the ME contribution arises from
 322 the superposition of contributions of different crystal planes under residual
 323 stress. Then, changing the deposition potential gives rise to microstructural
 324 changes and variations of the ME anisotropy of this segment. For instance,

325 no polycrystalline ME contribution is induced for $E = -1.3$ V, as seen in Fig.
326 (8) for the case of Ni NWs in PC membranes.

327 Furthermore, since the observed changes in K_{me} vs E for Ni NWs in AAO
328 membranes (see Fig. 8) arise only from variations of the ME contribution
329 of the polycrystalline segment, the strong positive ME contribution of the
330 single-crystalline segment is invariant to changes in the deposition potential.
331 Therefore, the large magnetic anisotropy enhancement in AAO based com-
332 posites can be always achieved regardless of the electrodeposition conditions,
333 with the only condition that long enough NWs have to be grown in order to
334 promote the nucleation of the single-crystalline segment.

335 Besides, for both AAO and PC based NW arrays the decrease of K_{me}
336 at $|E| > 1.3$ V, is related with the structure evolution from compact to-
337 wards more porous structure due to the enhanced electrochemical hydrogen
338 evolution [55, 32, 37]. The same feature is found for PC and AAO-based
339 NW arrays which leads to a similar reduction of the magnetostatic coupling
340 and corresponding magnetic anisotropy, as shown in Fig.8. However, for
341 AAO-based NW arrays, the estimated value of K_{me} remains positive follow-
342 ing the dominant contribution of the ME effect associated to the presence of
343 single-crystalline segment. Moreover, from the lowest to the highest potential
344 we observe that their magnetic anisotropy contribution increases, reaches a
345 maximum value and then decreases. This variation is consistent with the
346 behavior of the coercivity and remanence in the major hysteresis loop.

347 In general, the main phases observed in Ni NWs are (111), (220) and
348 (200). As expected, NWs grown in AAO membranes are consistent with the
349 presence of the (220) plane. While PC based NWs are mostly polycrystalline,
350 they also show a correlation between the increase of the amount of (111)
351 grains and the decrease in their anisotropy.

352 The structural changes in the Ni NWs due to the deposition potential
353 can be explained by a complex interplay between a hydrogen adsorption, the
354 surface energy and work function of various crystal planes [38, 56]. During
355 the electrochemical process, there are different reactions of the competitive
356 discharge between Ni^{2+} and H^+ ions [57, 55]. This growth competition and
357 the variation of the applied potential leads to a change in the composition
358 of the NWs that is associated with the predominance inside of the cathodic
359 layer of chemical species which results from the hydrogen co-deposition. As
360 observed, long NWs (AAO) are single-crystalline with a preferential growth
361 along the [110] direction, which is more favorable due to the fact that both
362 its work function and the H^+ ions absorption are low for this plane [58].

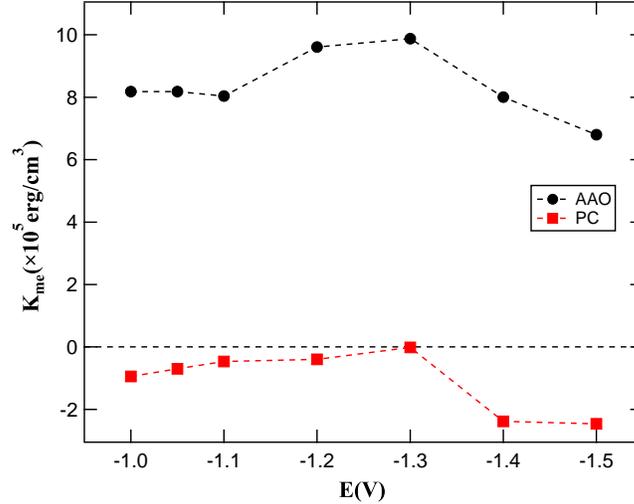


Figure 8: Variation of the magnetoelastic anisotropy energy K_{me} with the applied potential for Ni NWs grown in AAO and PC templates.

363 Moreover, the intensity of this plane is predominant regardless the applied
 364 potential. Conversely, short NWs (PC) grown at high potentials present a
 365 polycrystalline structure, which is in agreement with the Ni-fcc polycrys-
 366 talline face [59]. Changes in the NWs crystal structure are related with the
 367 variation of the deposition potential, which influences the growth nucleation
 368 rate of Ni ions. Then, the growth of the polycrystalline segment with the
 369 more pronounced peak corresponding to the (111) plane, is favoured at ions
 370 larger deposition rates due to the absence of active sites or blocking of metal
 371 by hydrogen bubbles during the electrodeposition process, which fairly ex-
 372 plains the behavior of Ni NWs grown at deposition potentials $|E| > 1.3$ V
 373 [32, 38].

374 5. Conclusion

375 The effect of the deposition potential on the structural and magnetic prop-
 376 erties of Ni NWs have been studied with particular interest in the enhanced
 377 uniaxial magnetic anisotropy obtained in very long NWs. To this end Ni
 378 NWs grown in AAO and PC nanoporous templates were considered. For the
 379 longest Ni NWs grown in AAO, two distinct structural phases are obtained.
 380 First a polycrystalline phase grows during the first stage of deposition, which

381 after attaining a certain critical length changes to a single-crystalline struc-
382 ture with a preferential orientation in the [110] direction. This two-stage
383 growth mechanism leads to the enhanced magnetic anisotropy. The results
384 show that once the microstructure changes from poly to single crystal the
385 enhancement of the magnetic anisotropy is practically insensitive to the de-
386 position potential. On the contrary, as seen for the shorter NWs grown in
387 PC templates, when the critical length where the structure changes from
388 poly to single crystal is not reached, there is no enhancement of the mag-
389 netic anisotropy. Moreover, the polycrystalline segment of the Ni deposits is
390 affected by the deposition potential. Our results show that the large uniaxial
391 magnetic anisotropy in arrays of Ni NWs have an inherent relation with their
392 size and confinement, this provide an interesting tool to develop nanoscale
393 materials with high magnetic anisotropy.

394 **Acknowledgements**

395 The authors thank R. Legras and E. Ferain of it4ip S. A. for provid-
396 ing the PC membranes as well as LINAN-IPICYT for access to their facil-
397 ities and Beatriz Rivera Escoto for her technical assistance with the XRD.
398 Y. Velázquez-Galván thanks Fondo CONACYT- Secretaría de Energía -
399 Hidrocarburos. This work was partly supported by CONACYT projects
400 CB-177896 and CB-286626, the UNAM-PAPIIT IN106619, the Fédération
401 Wallonie-Bruxelles (ARC 13/18-052, Supracryst) and the National Fund for
402 Scientific Research (FNRS).

- 403 [1] A. Huczko, *Appl. Phys. A*, 2000, **70**, 365.
- 404 [2] K. Nielsch, F. Müller, A.-P. Li and U. Gösele, *Adv. Mater.*, 2000, **12**,
405 582.
- 406 [3] C.-G. Wu, H. L. Li and N.-L. Shau, *J. Solid. State Electrochem.*, 2006,
407 **10**, 198.
- 408 [4] M. E. Toimil-Morales, *Beilstein J. Nanotechnol.*, 2012, **3**, 860–863.
- 409 [5] M. I. Irshad, F. Ahmad, N. M. Mohamed and M. Z. Abdullah, *Int. J.*
410 *Electrochem. Sci.*, 2014, **9**, 2548–2555.
- 411 [6] C. R. Martin, *Chem. Mater.*, 1996, **8**, 1739–1746.

- 412 [7] M. Kac, A. Zarzycki, S. Kac, M. Kopec, M. Perzanowski, E. M.
413 Dutkiewicz, K. Suchaneka, A. Maximenko and M. Marszalek, *Mater.*
414 *Sci. Eng., B*, 2016, **211**, 75–84.
- 415 [8] A. Vlad, V.-A. Antohe, J. M. Martinez-Huerta, E. Ferain, J.-F. Gohy
416 and L. Piraux, *J. Mater. Chem. A*, 2016, **4**, 1603.
- 417 [9] D. Su, H.-S. Kim, W.-S. Kim and G. Wang, *Chem. Eur. J.*, 2012, **18**,
418 8224–8229.
- 419 [10] S. Xu, C. Su, T. Wang, Y. Ma, J. Hu, J. Hu, N. Hu, Y. Su, Y. Zhang
420 and Z. Yang, *Electrochim. Acta*, 2018, **259**, 617–625.
- 421 [11] X. Niu, M. Lan, H. Zhao and C. Chen, *Anal. Chem.*, 2013, **85**, 3561–
422 3569.
- 423 [12] K. E. Toghill and R. G. Compton, *Int. J. Electrochem. Sci.*, 2010, **5**,
424 1246–1301.
- 425 [13] X. Wang, Y. Zhang, C. E. Banks, Q. Chen and X. Ji, *Colloids Surf., B*,
426 2010, **78**, 363–366.
- 427 [14] F. Guo, K. Ye, K. Cheng, G. Wang and D. Cao, *J. Power Sources*, 2015,
428 **278**, 562–568.
- 429 [15] J. Hubalek, J. Hradecky, V. Adam, O. Krystofova, D. Huska,
430 M. Masarik, L. Trnkova, A. Horna, K. Klosova, M. Adamek, J. Zehnalek
431 and R. Kizek, *Sensors*, 2007, **7**, 1238–1255.
- 432 [16] V. Vedharathinam and G. G. Botte, *Electrochim. Acta*, 2012, **81**, 292–
433 300.
- 434 [17] S. Dubois, J. Colin, J. L. Duvail and L. Piraux, *Phys. Rev. B*, 2000, **61**,
435 14315–14318.
- 436 [18] L. Piraux, G. Hamoir, A. Encinas, J. de la Torre Medina and F. A.
437 Araujo, *J. Appl. Phys.*, 2013, **114**, 123907.
- 438 [19] A. Ghaddar, J. Gieraltowski, F. Gloaguen, R. Zuberek, P. Aleshkevych,
439 J. Kazmierczak, A. Slawska-Waniewska and H. Szymczak, *Acta Phys.*
440 *Pol. A*, 2009, **116**, 1039–1043.

- 441 [20] C. T. Sousa, D. C. Leitaó, M. P. Proença, J. Ventura, A. M. Pereira and
442 J. P. Araujo, *Appl. Phys. Rev.*, 2014, **1**, 031102.
- 443 [21] L. Sun, P. C. Searson and C. L. Chien, *Phys. Rev. B*, 2000, **61**, R6463–
444 6466.
- 445 [22] X. W. Wang, G. T. Fei, X. J. Xu, Z. Jin and L. D. Zhang, *J. Phys.*
446 *Chem. B*, 2005, **109**, 24326–24330.
- 447 [23] H. Pan, B. Liu, J. Yi, C. Poh, S. Lim, J. Ding, Y. Feng, C. H. A. Huan,
448 and J. Lin, *J. Phys. Chem. B*, 2005, **109**, 3094–3098.
- 449 [24] K. Pitzschel, J. Bachmann, S. Martens, J. M. Montero-Moreno, J. Kim-
450 ling, G. Meier, J. Escrig, K. Nielsch and D. Görlitz, *J. Appl. Phys.*, 2011,
451 **109**, 033907.
- 452 [25] S. H. Xue and Z. D. Wang, *Mater. Sci. Eng., B*, 2006, **135**, 74–77.
- 453 [26] S. Karim and K. Maaz, *Mater. Chem. Phys.*, 2011, **130**, 1103 – 1108.
- 454 [27] B. Toal, M. McMillen, A. Murphy, W. Hendren, R. Atkinson and R. Pol-
455 lard, *Mater. Res. Express*, 2014, **1**, 015801.
- 456 [28] M. Motoyama, Y. Fukunaka, T. Sakka and Y. H. Ogata, *J. Electrochem.*
457 *Soc.*, 2006, **153**, C502–C508.
- 458 [29] I. Rahman, K. Razeeb, M. Rahman and M. Kamruzzaman, *J. Magn.*
459 *Magn. Mater.*, 2003, **262**, 166–169.
- 460 [30] A. Cortés, G. Riveros, J. L. Palma, J. C. Denardin, R. E. Marotti, E. A.
461 Dalchiele and H. Gómez, *J. Nanosci. Nanotechnol.*, 2009, **9**, 1992–2000.
- 462 [31] K. M. Razeeb, F. M. F. Rhen and S. Roy, *J. Appl. Phys.*, 2009, **105**,
463 083922.
- 464 [32] K. S. Napolskii, I. V. Roslyakov, A. A. Eliseev, D. I. Petukhov, A. V.
465 Lukashin, S.-F. Chen, C.-P. Liu and G. A. Tsirlina, *Electrochim. Acta*,
466 2011, **56**, 2378 – 2384.
- 467 [33] S. Thongmee, H. Pang, J. Ding and J. Lin, *J. Magn. Magn. Mater.*,
468 2009, **321**, 2712 – 2716.

- 469 [34] F. Tian, Z. P. Huang and L. Whitmore, *Phys. Chem. Chem. Phys.*, 2012,
470 **14**, 8537–8541.
- 471 [35] M. P. Proenca, C. T. Sousa, J. Ventura, M. Vazquez and J. P. Araujo,
472 *Electrochim. Acta*, 2012, **72**, 215 – 221.
- 473 [36] J. de la Torre Medina, G. Hamoir, Y. Velázquez-Galván, S. Pouget,
474 H. Okuno, L. Vila, A. Encinas and L. Piraux, *Nanotechnology*, 2016,
475 **27**, 145702.
- 476 [37] Y. Yu, J. Li, J. Wang, X. Wu, C. Yu, T. Xu, B. Chang, H. Sun and
477 H. Arandiyán, *Catalyst*, 2019, **9**, 152.
- 478 [38] S. Dellis, A. Christoulaki, N. Spiliopoulos, D. L. Anastassopoulos and
479 A. A. Vradis, *J. Appl. Phys.*, 2013, **114**, 164308.
- 480 [39] H. S. Shin, J. Yu, J. Y. Song and H. M. Park, *Appl. Phys. Lett.*, 2009,
481 **94**, 011906.
- 482 [40] H. S. Shin, J. Yu, J. Y. Song, H. M. Park and Y.-S. Kim, *Appl. Phys.*
483 *Lett.*, 2010, **97**, 131903.
- 484 [41] X. W. Wang, G. T. Fei, L. Chen, X. J. Xu and L. D. Zhang, *Electrochem.*
485 *Solid-State Lett.*, 2007, **10**, E1–E3.
- 486 [42] S.-Z. Chu, K. Wada, S. Inoue and S.-I. Todoroki, *Chem. Mater.*, 2002,
487 **14**, 4595–4602.
- 488 [43] K. Nielsch, R. B. Wehrspohn, J. Barthel, J. Kirschner, S. F. Kronmüller,
489 T. Schweinböck, D. Weiss and U. Gösele, *J. Magn. Magn. Mater.*, 2002,
490 **249**, 234.
- 491 [44] C. A. Ross, M. Hwang, M. Shima, J. Y. Cheng, M. Farhoud, T. A.
492 Savas, H. I. Smith, W. Schwarzacher, F. M. Ross, M. Redjidal and F. B.
493 Humphrey, *Phys. Rev. B*, 2002, **65**, 144417.
- 494 [45] V. Vega, V. M. Prida, J. A. García and M. Vazquez, *Phys. Status Solidi*
495 *A*, 2011, **208**, 553 – 558.
- 496 [46] J. Zhang, X. Qin, B. Torre, H. Zeng and X.-H. Xu, *IEEE Trans. Magn.*,
497 2014, **50**, 2301504.

- 498 [47] A. Encinas-Oropesa, M. Demand, L. Piraux, I. Huynen and U. Ebels,
499 *Phys. Rev. B*, 2001, **63**, 104415.
- 500 [48] G. B. Harris, *Philos. Mag.*, 1952, **43**, 113 – 123.
- 501 [49] *ICDD PDA-4 Nickel, Card 00-004-0850*.
- 502 [50] E. Dalchiele, R. Marotti, A. Cortes, G. Riveros, H. Gómez, L. Martínez,
503 R. Romero, D. Leinen, F. Martin and J. Ramos-Barrado, *Physica E*,
504 2007, **37**, 184–188.
- 505 [51] A. Encinas, M. Demand, J. M. George and L. Piraux, *IEEE Trans.*
506 *Magn.*, 2002, **38**, 2574–2576.
- 507 [52] C. Kittel, *Introduction to Solid State Physics*, Wiley, New York, 6th
508 edn., 1986.
- 509 [53] M. Tan and X. Chen, *J. Electrochem. Soc.*, 2011, **159**, K15–K20.
- 510 [54] X. H. Huang, G. H. Li, G. Z. Sun, X. C. Dou, L. Li and L. X. Zheng,
511 *Nanoscale Res. Lett.*, 2010, **5**, 1057–1062.
- 512 [55] R. W. E Chassaing and, M Jousselein and, *J. Electroanal. Chem.*, 1983,
513 **157**, 75–88.
- 514 [56] F. Maurer, G. T. Fei, X. J. Xu, Z. Jin and L. D. Zhang, *Nanotechnology*,
515 2007, **18**, 135709.
- 516 [57] J. Amblard, I. Epelboin, M. Froment and G. Maurin, *J. Appl. Elec-*
517 *trochem.*, 1979, **9**, 233–242.
- 518 [58] M. Paunovic and M. Schlesinger, *Electrochemical Phase Formation and*
519 *Growth*, Wiley-Interfase, New Jersey, 2006.
- 520 [59] K. Lejaeghere, V. V. Speybroeck, G. V. Oost and S. Cottenier, *Crit.*
521 *Rev. Solid State Mater. Sci.*, 2014, **39**, 1.